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12 **CLAIMS:**

13 1. A capacitor fabrication method comprising:
14 forming a first capacitor electrode over a substrate, the first
15 electrode having an inner surface area per unit area and an outer
16 surface area per unit area that are both greater than an outer surface
17 area per unit area of the substrate;

18 forming a capacitor dielectric layer over the first electrode; and
19 forming a second capacitor electrode over the dielectric layer.

20 2. The method of claim 1 wherein the first electrode comprises
21 TiN.

22 3. The method of claim 1 further comprising forming rugged
23 polysilicon over the substrate, the first electrode being over the rugged
24 polysilicon.

25 4. The method of claim 3 wherein the rugged polysilicon is
26 undoped.

27 5. The method of claim 3 wherein the rugged polysilicon
28 comprises hemispherical grain polysilicon.

Sub D 6. The method of claim 3 wherein the forming the rugged polysilicon comprises using a seed density sufficiently small to yield at least some spaced apart grains.

Sub D 7. The method of claim 1 wherein the outer surface area of the first electrode is at least 30% greater than the outer surface area of the substrate.

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Sub D 8. The method of claim 1 wherein the forming the first electrode comprises:

11 chemisorbing a layer of a first precursor at least one monolayer thick over the substrate;
12 chemisorbing a layer of a second precursor at least one monolayer thick on the first precursor layer, a chemisorption product of the first and second precursor layers being comprised by the first electrode.

Sub D 9. The method of claim 1 wherein the dielectric layer comprises Ta_2O_5 , ZrO_2 , WO_3 , Al_2O_3 , HfO_2 , barium strontium titanate, or strontium titanate.

1 10. A capacitor fabrication method comprising:

2 forming an opening in an insulative layer over a substrate, the

3 opening having sides and a bottom;

4 forming a layer of polysilicon over the sides and bottom of the

5 opening;

6 removing the polysilicon layer from over the bottom of the

7 opening;

8 converting at least some of the polysilicon layer to hemispherical

9 grain polysilicon;

10 conformally forming a first capacitor electrode on the converted

11 polysilicon, the first electrode being sufficiently thin that the first

12 electrode has an outer surface area per unit area greater than an outer

13 surface area per unit area of the substrate underlying the first electrode;

14 forming a capacitor dielectric layer on the first electrode; and

15 forming a second capacitor electrode over the dielectric layer.

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17 11. The method of claim 10 wherein the hemispherical grain

18 polysilicon is undoped.

19 12. The method of claim 10 wherein the converting the

20 polysilicon comprises using a seed density sufficiently small to yield at

21 least some spaced apart grains.

13. The method of claim 10 wherein the forming the first electrode comprises:

chemisorbing a layer of a first precursor at least one monolayer thick on the converted polysilicon;

chemisorbing a layer of a second precursor at least one monolayer thick on the first precursor layer; a chemisorption product of the first and second precursor layers being comprised by the first electrode.

14. The method of claim 10 wherein the first electrode comprises

15. The method of claim 10 wherein the dielectric layer comprises Ta_2O_5 , ZrO_2 , WO_3 , Al_2O_3 , HfO_2 , barium strontium titanate, or strontium titanate.

1 16. A capacitor construction comprising:

2 a first capacitor electrode over a substrate, the first electrode
3 having an inner surface area per unit area and an outer surface area per
4 unit area that are both greater than an outer surface area per unit area
5 of the substrate;

6 a capacitor dielectric layer over the first electrode; and

7 a second capacitor electrode over the dielectric layer.

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9 17. The construction of claim 16 wherein the first electrode
10 comprises TiN.

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12 18. The construction of claim 16 further comprising rugged
13 polysilicon over the substrate, the first electrode being over the rugged
14 polysilicon.

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16 19. The construction of claim 18 wherein the rugged polysilicon
17 is undoped.

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19 20. The construction of claim 18 wherein the rugged polysilicon
20 comprises spaced apart grains.

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21. The construction of claim 16 wherein the outer surface area
2 of the first electrode is at least 30% greater than the substrate outer
3 surface area.

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1 22. A capacitor construction comprising:

2 an opening in an insulative layer over a substrate, the opening

3 having sides and a bottom;

4 a hemispherical grain polysilicon layer over the sides of the

5 opening but not over the bottom;

6 a conformal first capacitor electrode on the polysilicon, the first

7 electrode being sufficiently thin that the first electrode has a rugged

8 outer surface with an outer surface area per unit area greater than an

9 outer surface area per unit area of the substrate underlying the first

10 electrode;

11 a capacitor dielectric layer on the first electrode; and

12 a second capacitor electrode over the dielectric layer.

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14 23. The construction of claim 22 wherein the polysilicon is

15 undoped.

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17 24. The construction of claim 22 wherein the polysilicon

18 comprises spaced apart grains.

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20 25. The construction of claim 22 wherein the first electrode

21 comprises TiN.

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26. The construction of claim 22 wherein the dielectric layer
2 comprises Ta_2O_5 , ZrO_2 , WO_3 , Al_2O_3 , HfO_2 , barium strontium titanate, or
3 strontium titanate

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